SGS-THOMSON MICROELECTRONICS

L6570A L6570B

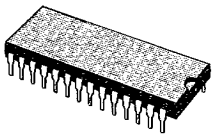
S G S-THOMSON

2–CHANNEL FLOPPY DISK READ/ WRITE CIRCUITS

- TWO GAIN VERSIONS (A AND B)
- COMPATIBLE WITH 8", 5.25" AND 3.5" DRIVES.
- INTERNAL WRITE AND ERASE CURRENT SOURCES, EXTERNALLY SET
- INTERNAL CENTER TAP VOLTAGE SOURCE
- CONTROL SIGNALS ARE TTL COMPATIBLE
- TTL SELECTABLE WRITE CURRENT BOOST
- OPERATES ON + 12 V AND + 5 V POWER SUPPLIES

DESCRIPTION

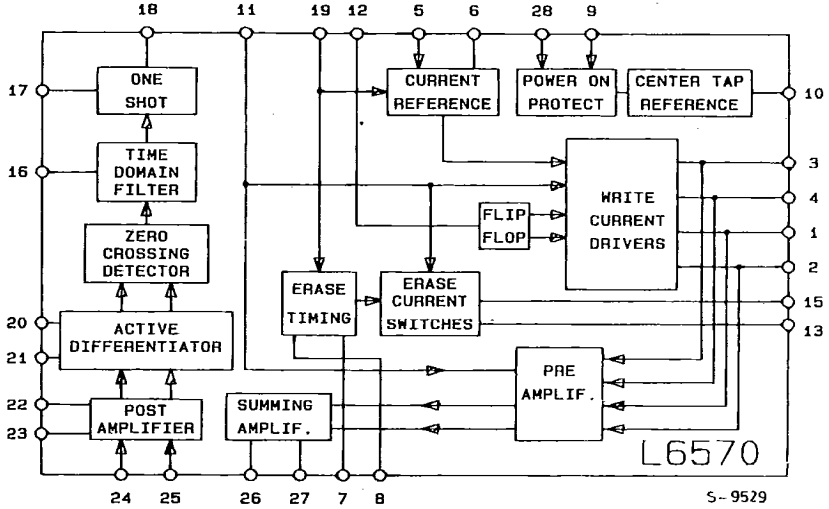
The L6570A/ B are integrated circuits which perform the functions of generating write signals and amplifying and processing read signals required for a double sided floppy disk drive. The L6570A features a gain of 85 min and the L6570B of 300 min. All logic inputs and outputs are TTL compatible and all timing is externally programmable for maximum design flexibility.



DIP–28 Plastic

ORDER CODES : L6570A
L6570B

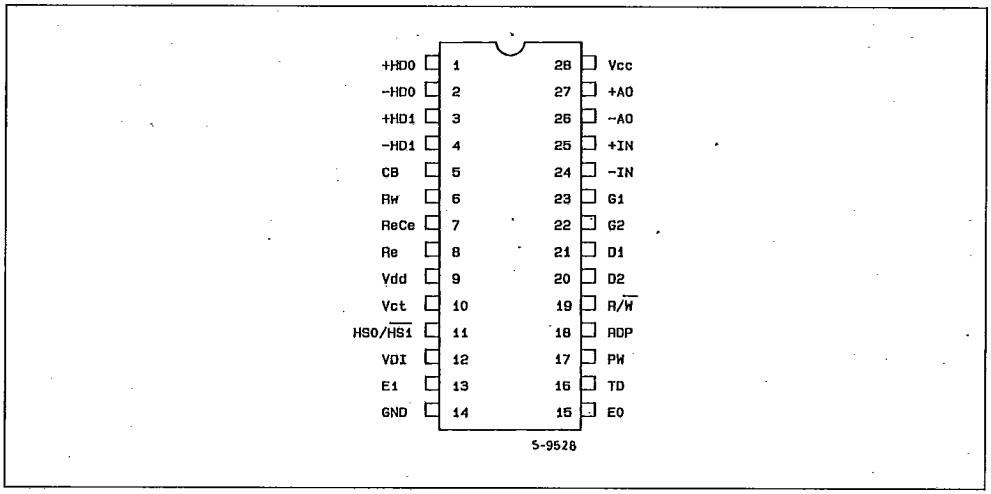
BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Test Conditions	Unit
V_{CC}	5V Supply Voltage	7	V
V_{DD}	12V Supply Voltage	14	V
T_{stg}	Storage Temperature	– 65 to 150	°C
T_{amb}	Ambient Operating Temperature	0 to + 70	°C
T_j	Junction Operating Temperature	0 to + 130	°C
V_I	Logic Input Voltage	– 0.5 to 7.0	V
P_{tot}	Power Dissipation	500	mW

CONNECTION DIAGRAM (top view)



THERMAL DATA

$R_{th\ j\text{-}amb}$	Thermal Resistance Junction-ambient	Max	100	°C/W

ELECTRICAL CHARACTERISTICS (unless otherwise specified, 4.75V ≤ V_{CC} ≤ 5.25V ; 11.4V ≤ V_{DD} ≤ 12,6V ; 0 °C ≤ T_{amb} ≤ 70 °C ; R_W = 430 Ω ; R_{ED} = 62 KΩ ; C_E = 0.012 µF ; R_{EH} = 62 KΩ ; R_{EC} =220Ω)

Symbol	Parameter	Test Condtions	Min.	Typ.	Max.	Unit
POWER SUPPLY CURRENTS						
I_{CC}	5V Supply Current	Read Mode Write Mode			35 38	mA mA
I_{DD}	12V Supply Current	Read Mode **L6570A** **L6570B**			26 35	mA mA
		Write Mode (exclude Write and Erase currents) **L6570A** **L6570B**			24 35	mA mA
LOGIC SIGNALS-READ/$\overline{\text{WRITE}}$ (R/$\overline{\text{W}}$), CURRENT BOOST (CB)						
V_{IL}	Input Low Voltage				0.8	V
I_{IL}	Input Low Current	V_{IL} = 0.4V			– 0.4	mA
V_{IH}	Input High Voltage		2.0			V
I_{IH}	Input High Current	V_{IH} = 2.4V			20	µA
LOGIC SIGNALS-WRITE DATA INPUT (WDI), **HEAD SELECT** (HS0/HS1)						
V_{T+}	Threshold Voltage, Positive-going		1.4		1.9	V
V_{T-}	Threshold Voltage, Negative-going		0.6		1.1	V
V_{T+}, V_{T-}	Hysteresis		0.4			V
I_{IH}	Input High Current	V_{IH} = 2.4V			20	µA
I_{IL}	Input Low Current	V_{IL} = 0.4V			– 0.4	mA
CENTER TAP VOLTAGE REFERENCE						
V_{CT}	Output Voltage	I_{WC} + I_E = 3 mA to 60 mA	V_{DD}–1.5		V_{DD}–0.5	V
V_{CC}	Turn-Off Threshold		4.0			V
V_{DD}	Turn-Off Threshold		9.6			V
V_{CT}	Disabled Voltage				1.0	V
ERASE OUTPUTS (E1, E0)						
	Unselected Head Leakage	V_{EO}, V_{E1} = 12.6V			100	µA
V_{E1}, V_{EO}	Output on Voltage	I_E = 50 mA			0.5	V

ELECTRICAL CHARACTERISTICS (Continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
WRITE CURRENT						
	Unselected Head Leakage	V_{E1}, V_{E0} = 12.6V			25	µA
	Write Current Range	R_W = 820 Ω to180 Ω	3		10	mA
	Current Reference Accuracy	$I_{WC} = 2.3/R_W$ V_{CB} (current boost) = 0.5V	–5		+5	%
	Write Current Unbalanced	I_{WC} = 3 mA to 10 mA			1.0	%
	Differential Head Voltage Swing	$\Delta I_{WC} \leq 5$ %	12.8			V_{pk}
	Current Boost	V_{CB} = 2.4V	1.25 I_{WC}		1.35 I_{WC}	
ERASE TIMING						
	Erase Delay Range	R_{ED} = 39 KΩ to 82 KΩ C_E = 0.0015 µF to 0.043 µF	0.1		1.0	ms
	Erase Delay Accuracy $\frac{\Delta T_{ED}}{T_{ED}}$ x100 %	$T_{ED} = 0.69\ R_{ED}\ C_E$ R_{ED} = 39 KΩ to 82 KΩ C_E = 0.0015 µF to 0.043 µF	– 15		+ 15	%
	Erase Hold Range	$R_{EH} + R_{ED}$ = 78 KΩ to 164 KΩ C_E = 0.0015 µF to 0.043 µF	0.2		2.0	ms
	Erase Hold Accuracy $\frac{\Delta T_{ED}}{T_{ED}}$ x 100 %	$T_{EH} = 0.69\ (R_{ED} + R_{ED})\ C_E$ $R_{EH} + R_{ED}$ = 78 KΩ to 164 KΩ C_E = 0.0015 µF to 0.043 µF	– 15		+ 15	%

ELECTRICAL CHARACTERISTICS (Unless otherwise specified : V_{IN} (Preamplifier) =10mV_{pp} sine wave, DC coupled to center tap. Summing amplifier load = 2 KΩ line-line, AC coupled. V_{IN} (Postamplifier)= 0.2 V_{pp} sine wave, AC coupled ; R_G = open ; Data pulse load = 1 KΩ to V_{CC} ; C_D = 240 pF ; C_{TD} = 100 pF ; R_{TD} = 7.5 KΩ ; C_{PW} = 47 pF ; R_{PW} = 7.5 KΩ).

READ MODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
PREAMPLIFIER-SUMMING AMPLIFIER						
	Diff Voltage Gain	Freq. = 250 KHz **L6570A** **L6570B**	85 300		115 400	V/V
	Bandwidth (– 3 dB)		3			MHz
	Gain Flatness	Freq. = DC to 1.5 MHz			± 1.0	dB
	Diff. Input Impedance	Freq. = 250 KHz	20			KΩ
	Max. Diff. Output Voltage Swing	V_{IN} = 250 KHz Sine Wave THD ≤ 5 % **L6570A** **L6570B**	 2.5 4.0			V_{pp}
	Small Signal Difference Output Resistance	$I_O \leq 1.0$ mA $_{pp}$			75	Ω
	Common Mode Rejection Ratio	V_{IN} = 300 mV_{pp} @ 500 KHz Inputs Shorted **L6570A** **L6570B**	 50 40			dB

ELECTRICAL CHARACTERISTICS (Continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
PREAMPLIFIER-SUMMING AMPLIFIER						
	Power Supply Rejection Ratio	ΔV_{DD} = 300 mV_{pp} @ 500 KHz Inputs Shorted to V_{CT}	50			dB
	Channel Isolation	Unselected Channel V_{IN} =100 mV_{pp} @ 500 KHz. Selected Channel Input Connected to V_{CT}	40			dB
	Equivalent Input Noise	Power BW = 10 kHz to 1 MHz Inputs Shorted to V_{CT}			10	μV_{rms}
V_{CT}	Center Tap Voltage			1.5		V
POSTAMPLIFIER-ACTIVE DIFFERENTIATOR						
	AO, Diff. Voltage Gain + IN, - IN to D1, D2	Freq. = 250 KHz	8.5		11.5	V/V
	Bandwidth (– 3dB) + IN, - IN to D1, D2	C_D = 0.1 µF, R_D = 2.5 KΩ	3			MHz
	Gain Flatness + IN, - IN to D1, D2	Freq. = DC to 1.5 MHz C_D = 0.1 µF, R_D = 2.5 KΩ			± 1.0	dB
	Max. Diff. Output Voltage Swing	V_{IN} = 250 KHz Sine Wave, AC Coupled. ≤ 5 % THD in Voltage across C_D	5.0			V_{pp}
	Max. Diff. Input Voltage	V_{IN} = 250 KHz Sine Wave, AC Coupled. ≤ 5 % THD in Voltage across C_D, R_G = 1.5 KΩ	2.5			V_{pp}
	Diff. Input Impedance		10			KΩ
	Gain Control Accuracy $\frac{\Delta A_R}{A_R}$ x 100 %	$A_R = A_O R_G/(8 \times 10^3 + R_G)$ R_G = 2 KΩ	– 25		+ 25	%
	Threshold Differential Input Voltage	Min. diff. input voltage at post amp. that results in a change of state at RDP V_{IN} = 250 KHz square wave, C_D = 0.1 µF R_D = 500 Ω, T_R, T_F ≤ 0.2 µs. No overshoot ; Data pulse from each V_{IN} transition			3.7	mV_{pp}
	Peak Differential Network Current		1.0			mA

ELECTRICAL CHARACTERISTICS (Continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
TIME DOMAIN FILTER						
	Delay Accuracy $\frac{\Delta T_{TD}}{T_{TD}}$ x 100 %	$T_{TD} = 0.58\ R_{TD} \cdot (C_{TD} + 10^{-11}) + 150$ ns. $R_{TD} = 5$ KΩ to 10 KΩ $C_{TD} = 56$ pF $V_{IN} = 50\ mV_{pp}$ @ 250 KHz sq. wave $T_R, T_F \leq 20$ ns, AC coupled. Delay measured from 50 % input amplitude to 1.5 V data pulse	– 15		+ 15	%
	Delay Range	$T_{TD} = 0.58\ R_{TD} = (C_{TC} + 10^{-11}) + 150$ ns. $R_{TD} = 5$ KΩ to 10 KΩ $C_{TD} = 56$ pF to 240 pF $R_D = 500\ \Omega$ $C_D = 0.1\ \mu F$.	240		2370	ns
DATA PULSE						
	Width Accuracy $\frac{\Delta T_{PW}}{T_{PW}}$ x 100 %	$T_{PW} = 0.58\ R_{PW}$ x $(C_{PW} + 8 \times 10^{-12}) + 20$ ns $R_{PW} = 5$ KΩ to 10 KΩ $C_{PW} \geq 36$ pF with measured at 1.5V amplitudes	– 20		+ 20	%
	Active Level Output Voltage	$I_{OH} = 400\ \mu A$	2.7			V
	Inactive Level Output Leakage	$I_{OL} = 4$ mA			0.5	V
	Pulse Width	$T_{PW} = 0.58\ R_{PW}$ x $(C_{PW} + 8 \times 10^{-12}) + 20$ ns $R_{PW} = 5$ KΩ to 10 KΩ $C_{PW} = 36$ pF to 200 pF	145		1225	ns

TEST SCHEMATICS

Figure 1 : Preamplifier Characteristics.

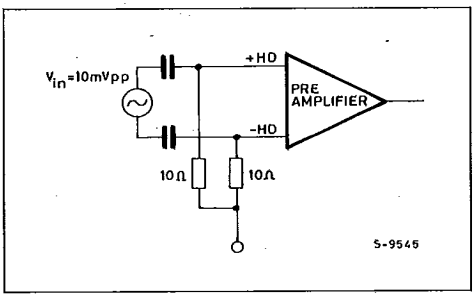
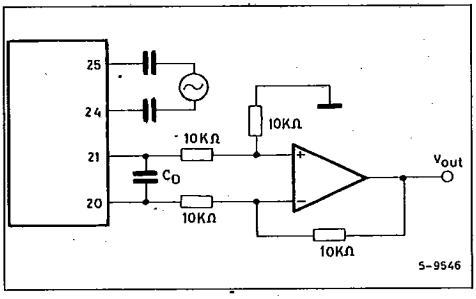


Figure 2 : Postamplifier Differential Output Voltage Swing and Voltage Gain.



TEST SCHEMATICS (Continued)

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Figure 3 : Postamplifier Threshold Differential Input Voltage.

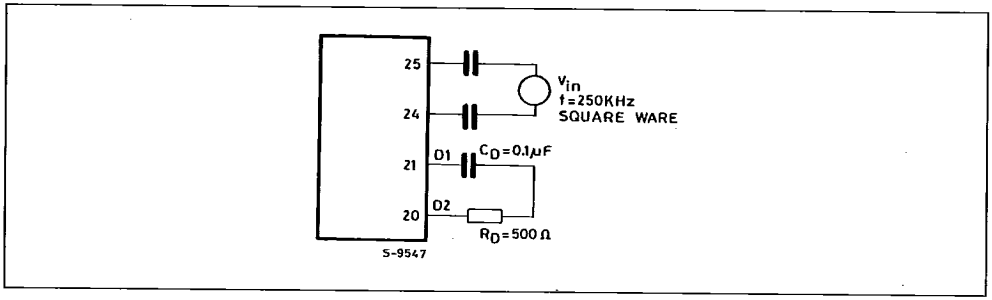

Figure 4 : Complete Test Circuit.